

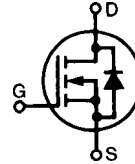
HiPerFET™ Power MOSFETs

IXFH 60N20
IXFT 60N20

$$\begin{aligned} V_{DSS} &= 200 \text{ V} \\ I_{D25} &= 60 \text{ A} \\ R_{DS(on)} &= 33 \text{ m}\Omega \end{aligned}$$

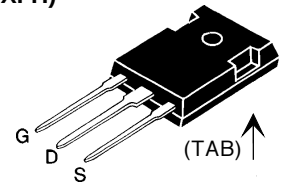
N-Channel Enhancement Mode
Avalanche Rated, High dv/dt

$$t_{rr} \leq 250 \text{ ns}$$

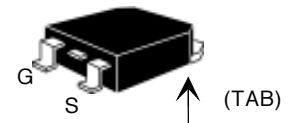


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	200	V
V_{DGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	200	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	60	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	240	A
I_{AR}	$T_C = 25^\circ\text{C}$	60	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}		2.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 to +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 to +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 AD (IXFH)



TO-268 (IXFT) Case Style



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$
- Rated for unclamped Inductive load switching (UIS)
- Molding epoxies meet UL 94 V-0 flammability classification

Advantages

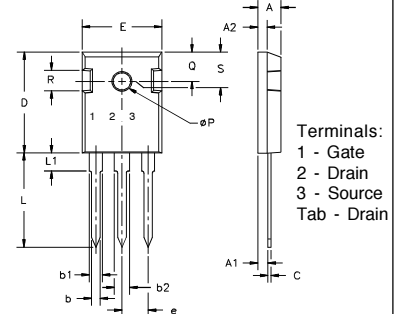
- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$	$T_J = 25^\circ\text{C}$		25 μA
	$V_{GS} = 0 \text{ V}$	$T_J = 125^\circ\text{C}$		1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			33 m Ω

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	V _{DS} = 10 V; I _D = 0.5 • I _{D25} , pulse test	30	40	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5200	pF
C_{oss}			880	pF
C_{rss}			260	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 2.5 Ω (External),		38	ns
t_r			63	ns
t_{d(off)}			85	ns
t_f			26	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		155	nC
Q_{gs}			38	nC
Q_{gd}			55	nC
R_{thJC}	(TO-247)		0.25	0.42 K/W
R_{thCK}				K/W

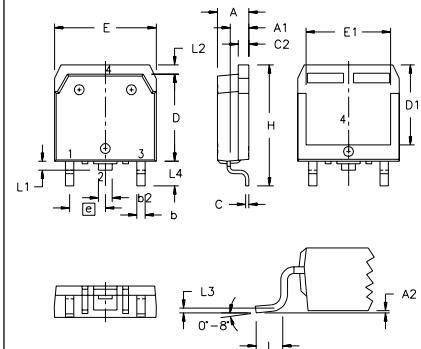
Source-Drain Diode		Characteristic Values (T _j = 25°C, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	V _{GS} = 0 V			60 A
I_{SM}	Repetitive; pulse width limited by T _{JM}			240 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
t_{rr}	I _F = 25A, -di/dt = 100 A/μs, V _R = 50 V		0.7 8	250 ns
Q_{RM}				μC
I_{RM}				A

TO-247 AD (IXFH) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025